

HL6316G

AlGaInP Laser Diodes

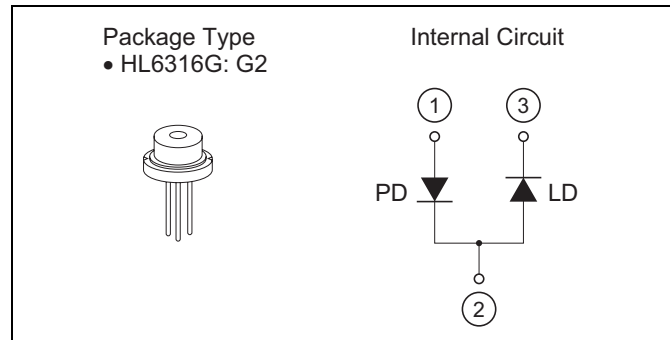
ODE-208-026 (Z)
Rev.0
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Description

The HL6316G is a 0.63 μm band AlGaInP laser diodes with a multi-quantum well (MQW) structure. It is suitable as light sources for laser pointers and optical equipment.

Features

- Visible light output: 635 nm Typ
- Single longitudinal mode
- Optical output power: 3 mW CW
- Low operating current: 30 mA Typ
- Low operating voltage: 2.7 V Max
- TM mode oscillation



Absolute Maximum Ratings

($T_C = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Optical output power	P_O	3	mW
Pulse optical output power	$P_{O(\text{pulse})}$	5 *	mW
LD reverse voltage	$V_{R(\text{LD})}$	2	V
PD reverse voltage	$V_{R(\text{PD})}$	30	V
Operating temperature	T_{opr}	-10 to +50	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +85	$^\circ\text{C}$

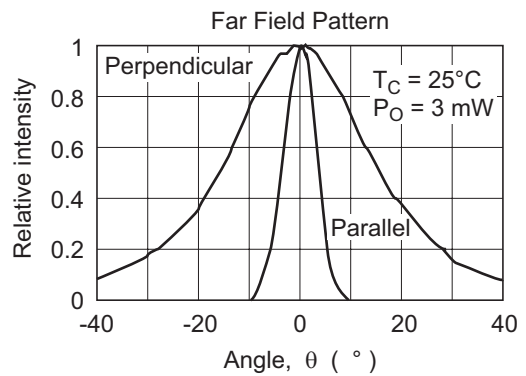
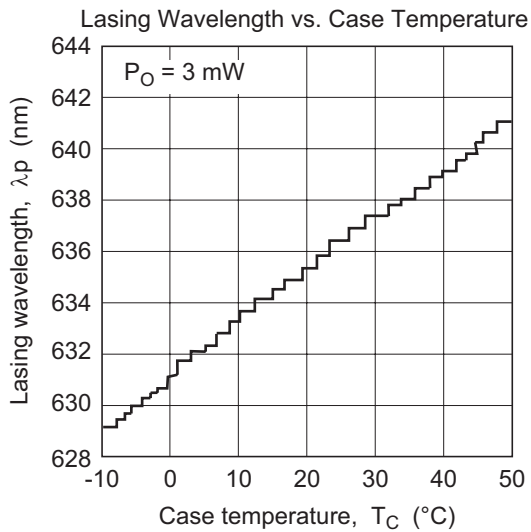
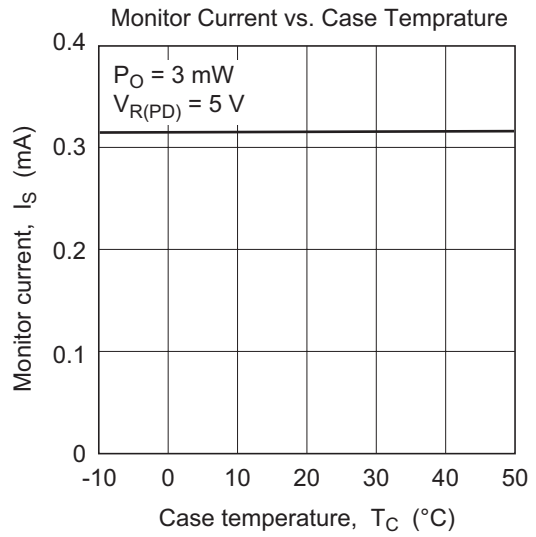
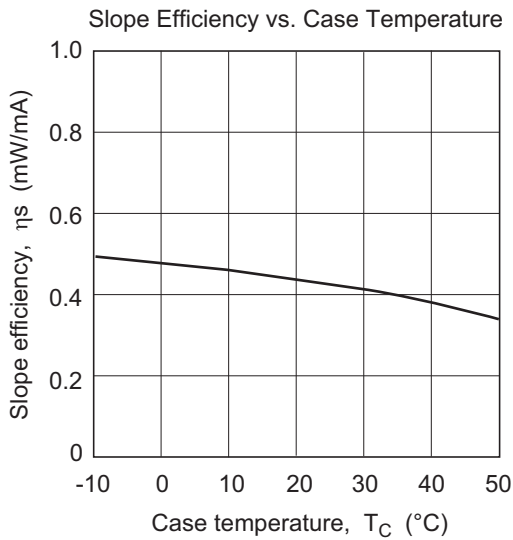
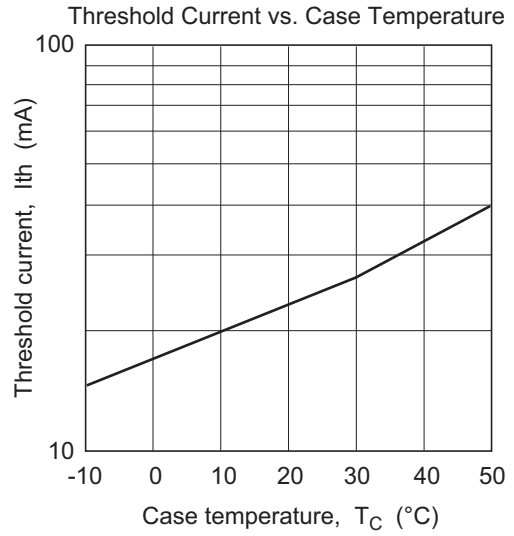
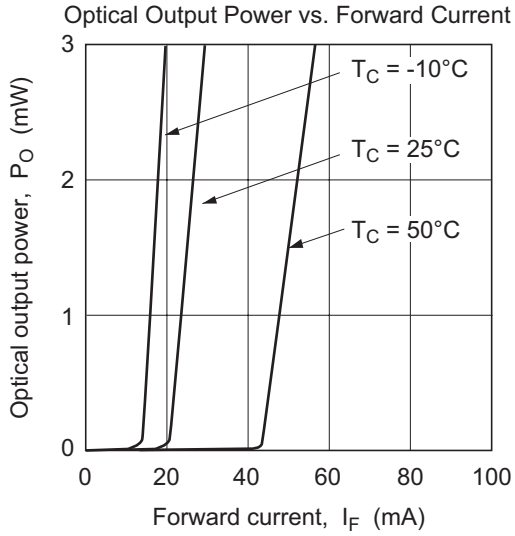
Note: Pulse condition : Pulse width $\leq 1 \mu\text{s}$, duty $\leq 50\%$

Optical and Electrical Characteristics

($T_C = 25^\circ\text{C}$)

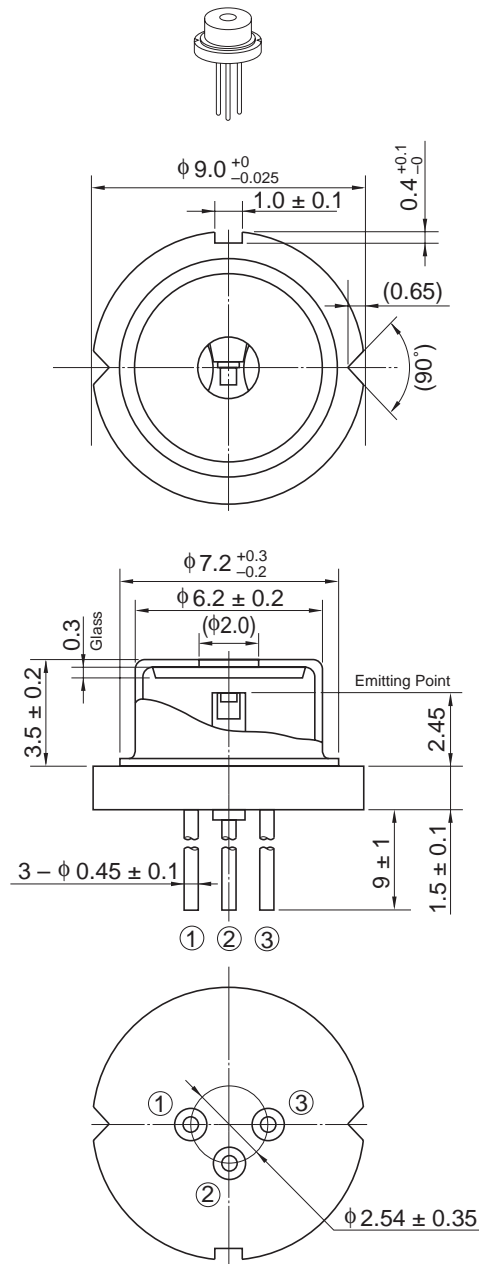
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Threshold current	I_{th}	—	25	35	mA	—
Operating current	I_{OP}	—	30	42	mA	$P_O = 3 \text{ mW}$
Operating voltage	V_{OP}	—	—	2.7	V	$P_O = 3 \text{ mW}$
Beam divergence parallel to the junction	$\theta_{//}$	6	8	10	$^\circ$	$P_O = 3 \text{ mW}$
Beam divergence perpendicular to the junction	θ_{\perp}	23	30	39	$^\circ$	$P_O = 3 \text{ mW}$
Lasing wavelength	λ_p	630	635	640	nm	$P_O = 3 \text{ mW}$
Monitor current	I_s	0.1	0.3	0.6	mA	$P_O = 3 \text{ mW}$, $V_{R(\text{PD})} = 5 \text{ V}$

Typical Characteristic Curves



Package Dimensions

As of July, 2002
Unit: mm



OPJ Code	LD/G2
JEDEC	—
JEITA	—
Mass (reference value)	1.1 g

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Sales Offices



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